

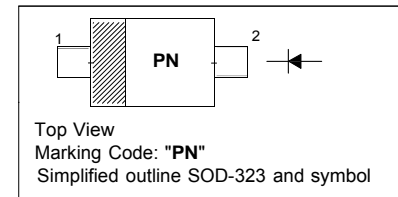
SILICON EPITAXIAL PLANAR DIODE

BAND SWITCHING DIODE

For band switching application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Forward Current	I_F	100	mA
Operating Ambient Temperature ¹⁾	T_{opr}	- 25 to + 85	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

¹⁾ Maximum ambient temperature during operation

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1	V
Reverse Current at $V_R = 33\text{ V}$	I_R	0.1	μA
Diode Capacitance at $V_R = 6\text{ V}$, $f = 1\text{ MHz}$	C_D	1.2	pF
Forward Dynamic Resistance at $I_F = 2\text{ mA}$, $f = 100\text{ MHz}$	r_f	0.85	Ω



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